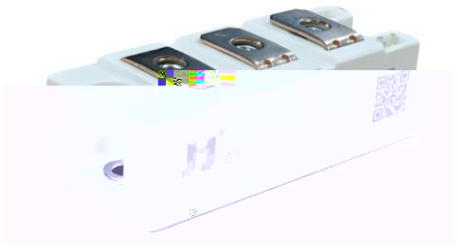
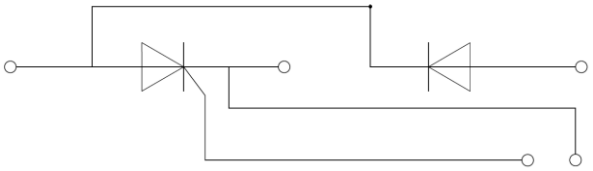
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FIG 1:Power dissipation vs. on-state current

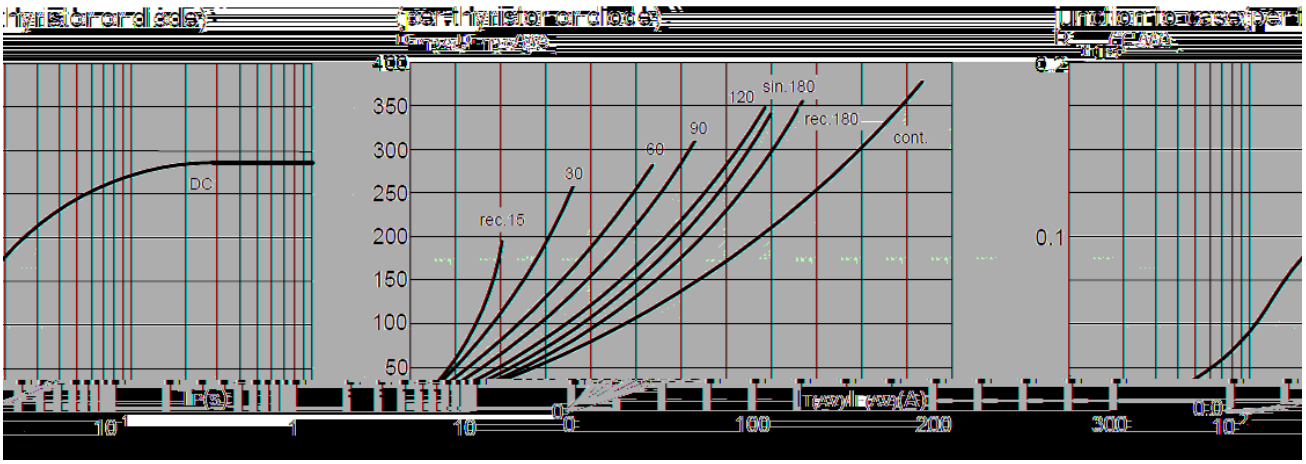



FIG 2: Maximum transient thermal impedance

FIG 3:Forward characteristics (per thyristor or diode)

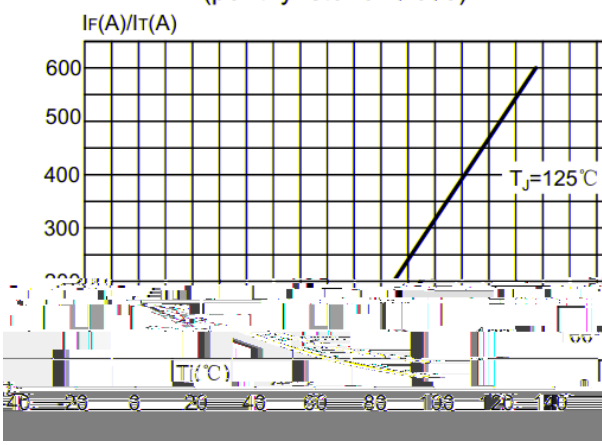



FIG 4: Relative variation of gate trigger current, holding current and latching current versus junction temperature

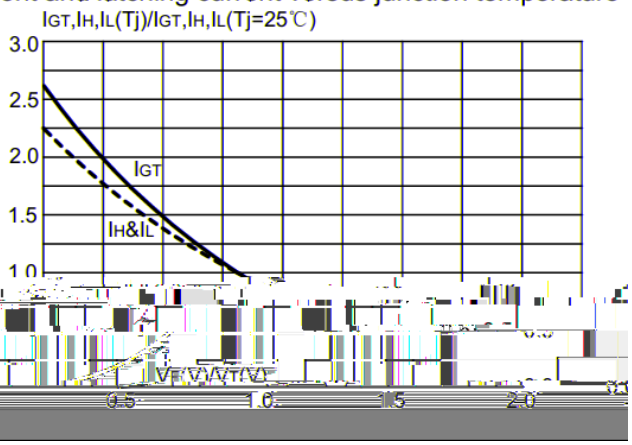



FIG 5 Gate trigger characteristics

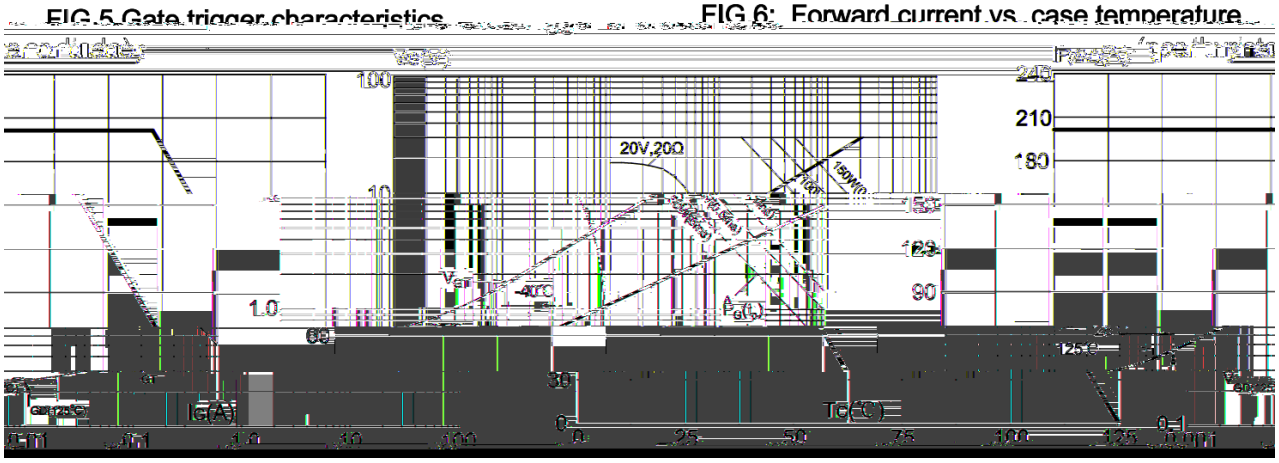



FIG 6: Forward current vs. case temperature